

1. Scope :

This specification applies to PN silicon photodiode chips,
Device NO. PD-0340.

2. Structure :

2-1. Planar type : PN Diode.

2-2. Electrodes :

Top side (Anode) : Aluminum alloy .

Back side (Cathode) : Gold alloy .

3. Size :

3-1. Chip size : 40 mils × 40 mils (1.016 mm × 1.016 mm).

3-2. Chip thickness : 8.6 ± 1.2 mils (0.220 ± 0.030 mm).

3-3. Active area : 32 mils × 32 mils (0.813 mm × 0.813 mm).

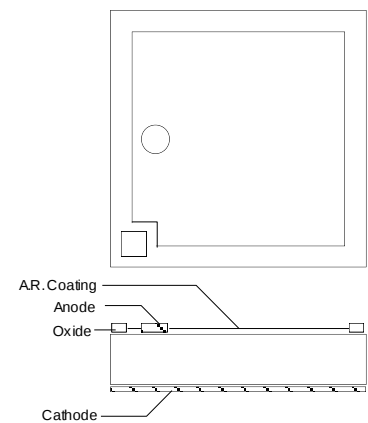
3-4. Bonding pad (Anode) : 5.4 mils (0.137 mm) Diameter.

3-5. Pattern drawing : Refer to the attached drawing.

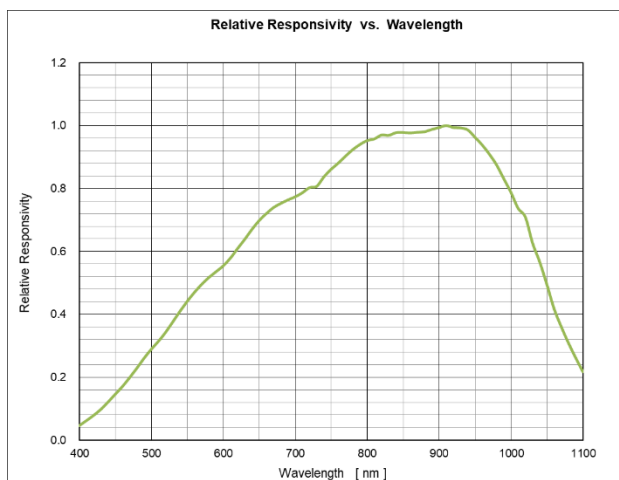
4. Electro-optical characteristics (Ta = 25 °C)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Reverse dark current	I_D	$V_R=10V$ $E_e=0mW/cm^2$			10	nA
Reverse breakdown voltage	$V_{(BR)R}$	$I_R=100\mu A$ $E_e=0mW/cm^2$	33			V
Open circuit voltage	V_{oc}	$T=2856K$ $E_e=5mW/cm^2$		440		mV
Short circuit Current	I_{sc}	$T=2856K$ $E_e=5mW/cm^2$		7		μA
Reverse light current	I_L	$V_R = 5V$ $T=2856K$ $E_e=5mW/cm^2$		7		μA
Total Capacitance	C_T	$V_R = 5V$ $E_e=0mW/cm^2$ $f=1MHz$		10		pF

*Based on 100% probing



5. Relative spectral responsivity



*Bare chip measured with integrating sphere, for reference only.